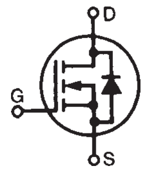
IXYS

Polar3™ HiperFET™ Power MOSFET

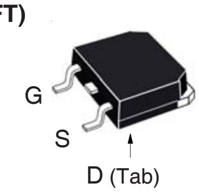
IXFT50N50P3
IXFQ50N50P3
IXFH50N50P3

V_{DSS} = 500V
I_{D25} = 50A
$R_{DS(on)}$ ≤ 125mΩ

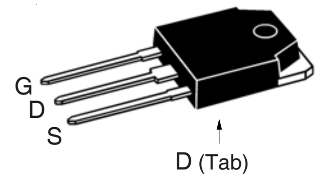
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier



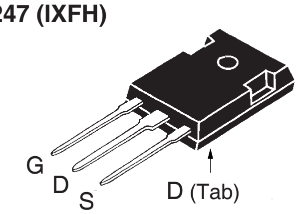
TO-268 (IXFT)



TO-3P (IXFQ)



TO-247 (IXFH)



G = Gate　D = Drain
S = Source　Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T_C = 25°C	50	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	150	A
I_A	T_C = 25°C	25	A
E_{AS}	T_C = 25°C	500	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	35	V/ns
P_D	T_C = 25°C	960	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-247 & TO-3P)	1.13 / 10	Nm/lb.in
Weight	TO-268	4.0	g
	TO-3P	5.5	g
	TO-247	6.0	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	500			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 4mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = V_{DSS}, V_{GS} = 0V			25	μA
	T_J = 125°C			1.5	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.5 • I_{D25}, Note 1			125	mΩ

Features

- Fast Intrinsic Rectifier
- Avalanche Rated
- Low $R_{DS(ON)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

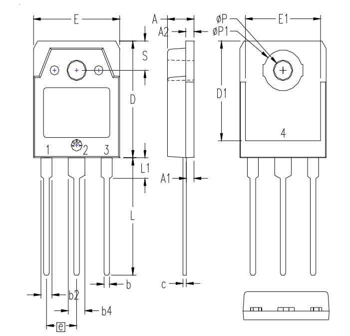
Symbol	Test Conditions ($T_J = 25°C$ Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	$V_{DS} = 20V$, $I_D = 0.5 \bullet I_{D25}$, Note 1	27	45		S
C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, f = 1MHz		4335		pF
C_{oss}			540		pF
C_{rss}			12		pF
R_{Gi}	Gate Input Resistance		1.4		Ω
$t_{d(on)}$	**Resistive Switching Times**		25		ns
t_r	$V_{GS} = 10V$, $V_{DS} = 0.5 \bullet V_{DSS}$, $I_D = 0.5 \bullet I_{D25}$		8		ns
$t_{d(off)}$	$R_G = 2\Omega$ (External)		53		ns
t_f			10		ns
$Q_{g(on)}$	$V_{GS} = 10V$, $V_{DS} = 0.5 \bullet V_{DSS}$, $I_D = 0.5 \bullet I_{D25}$		85		nC
Q_{gs}			21		nC
Q_{gd}			30		nC
R_{thJC}				0.13	°C/W
R_{thCS}	(TO-247 & TO-3P)		0.25		°C/W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25°C$ Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	$V_{GS} = 0V$			50	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			200	A
V_{SD}	$I_F = I_S$, $V_{GS} = 0V$, Note 1			1.4	V
t_{rr}	$I_F = 25A$, -di/dt = 100A/µs			250	ns
I_{RM}	$V_R = 100V$, $V_{GS} = 0V$		12		A
Q_{RM}			880		nC

Note 1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.

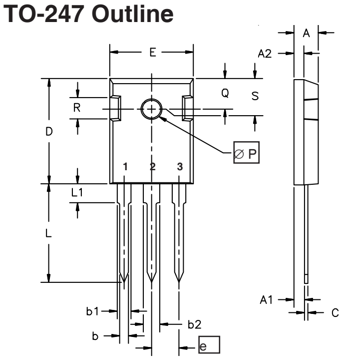
TO-3P Outline



1 – GATE
2 – DRAIN
3 – SOURCE
4 – DRAIN

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

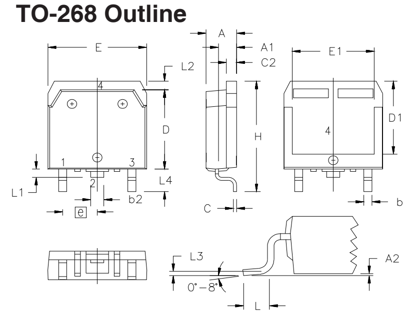
TO-247 Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



Terminals: 1 - Gate 2,4 - Drain
3 - Source

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ $T_J = 25^oC$

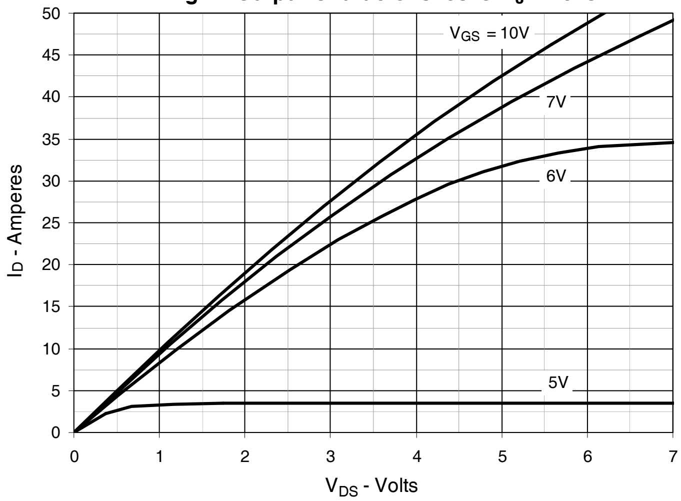


Fig. 2. Extended Output Characteristics @ $T_J = 25^oC$

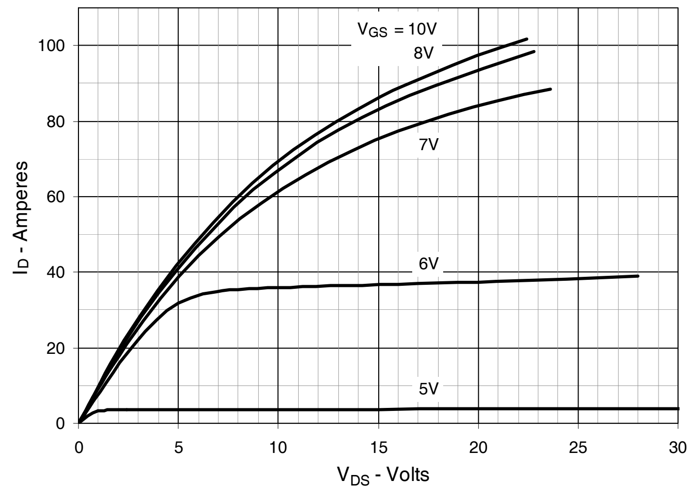


Fig. 3. Output Characteristics @ $T_J = 125^oC$

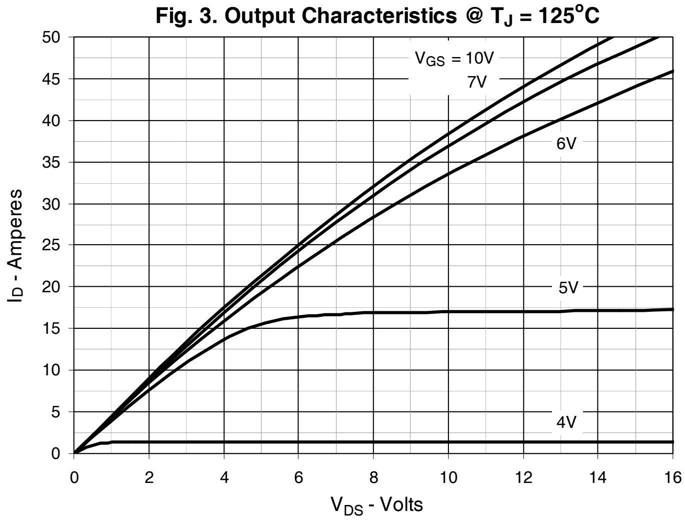


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 25A Value vs. Junction Temperature

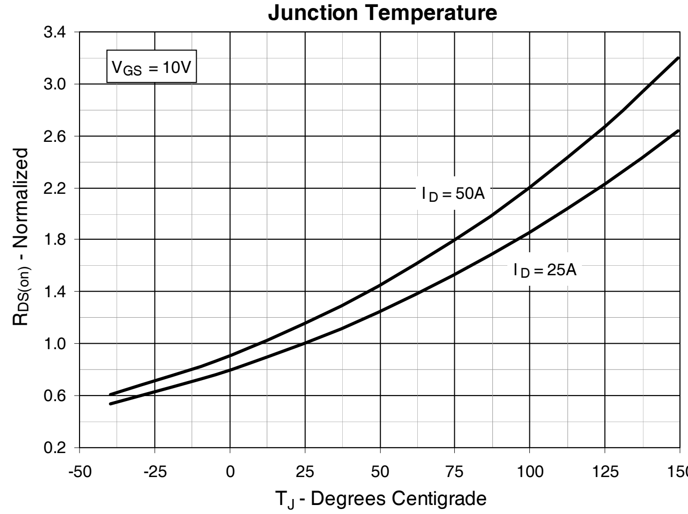


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 25A Value vs. Drain Current

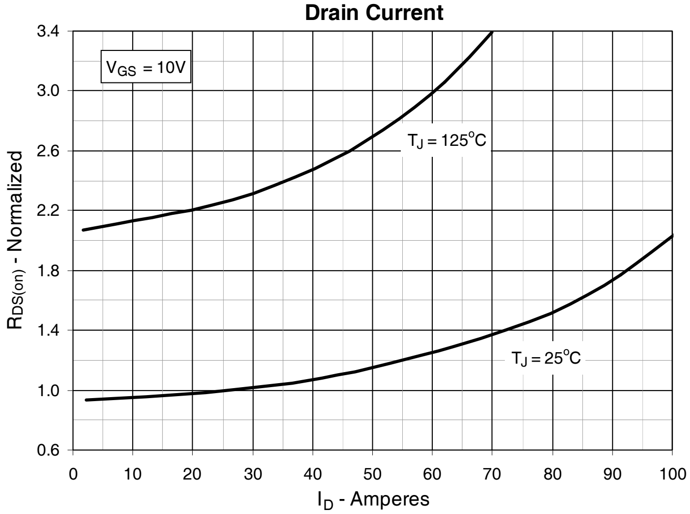


Fig. 6. Maximum Drain Current vs. Case Temperature

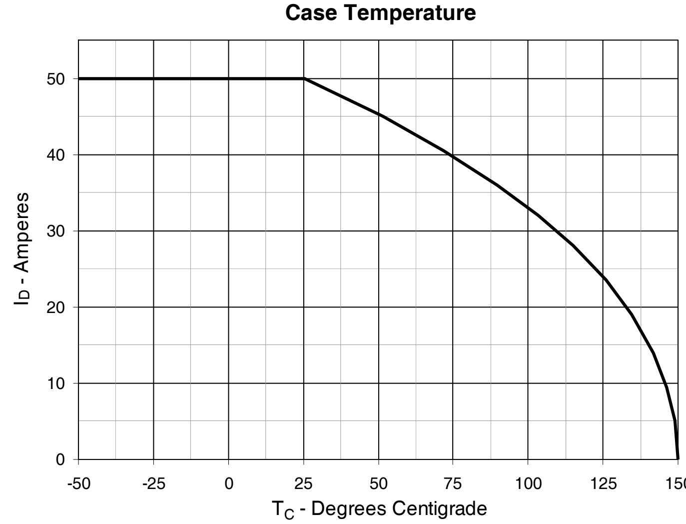


Fig. 7. Input Admittance

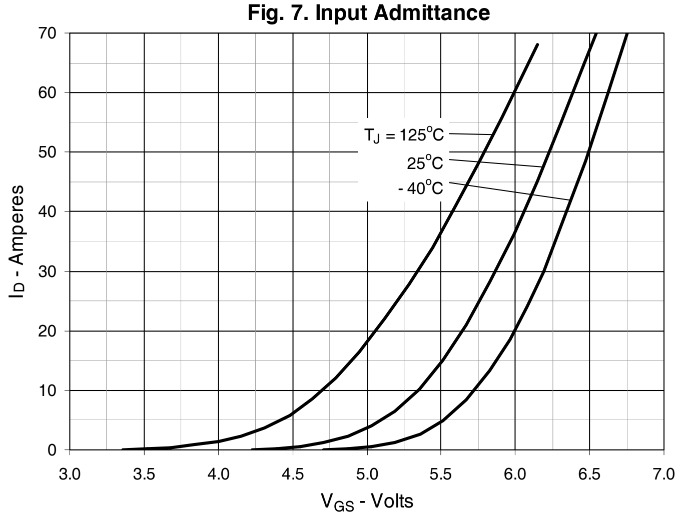


Fig. 8. Transconductance

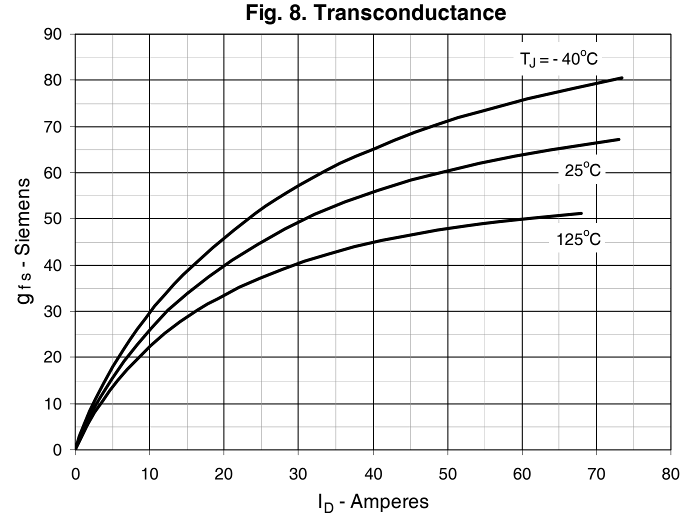


Fig. 9. Forward Voltage Drop of Intrinsic Diode

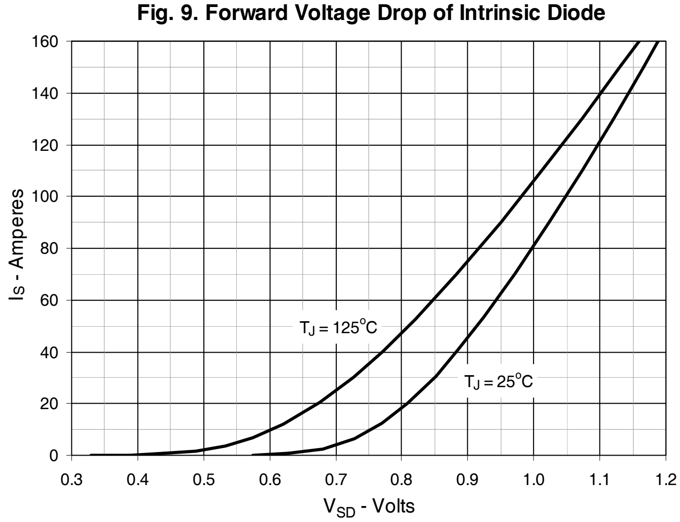


Fig. 10. Gate Charge

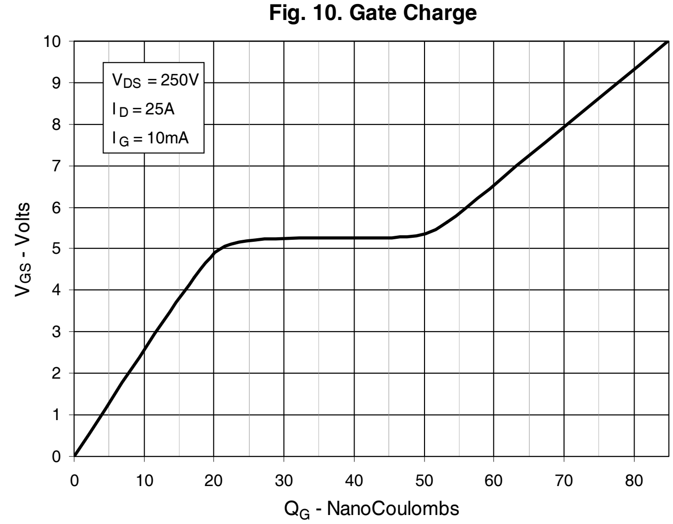


Fig. 11. Capacitance

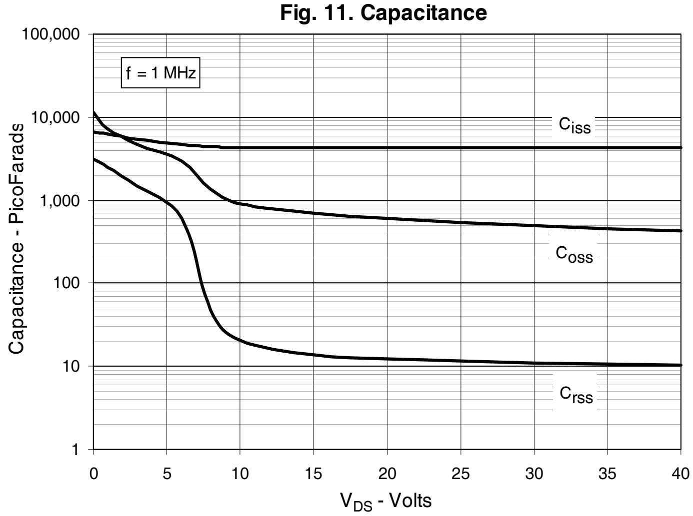


Fig. 12. Forward-Bias Safe Operating Area

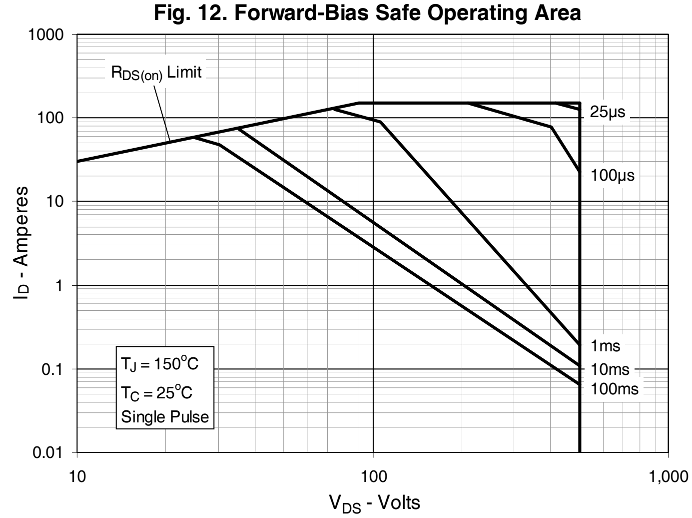


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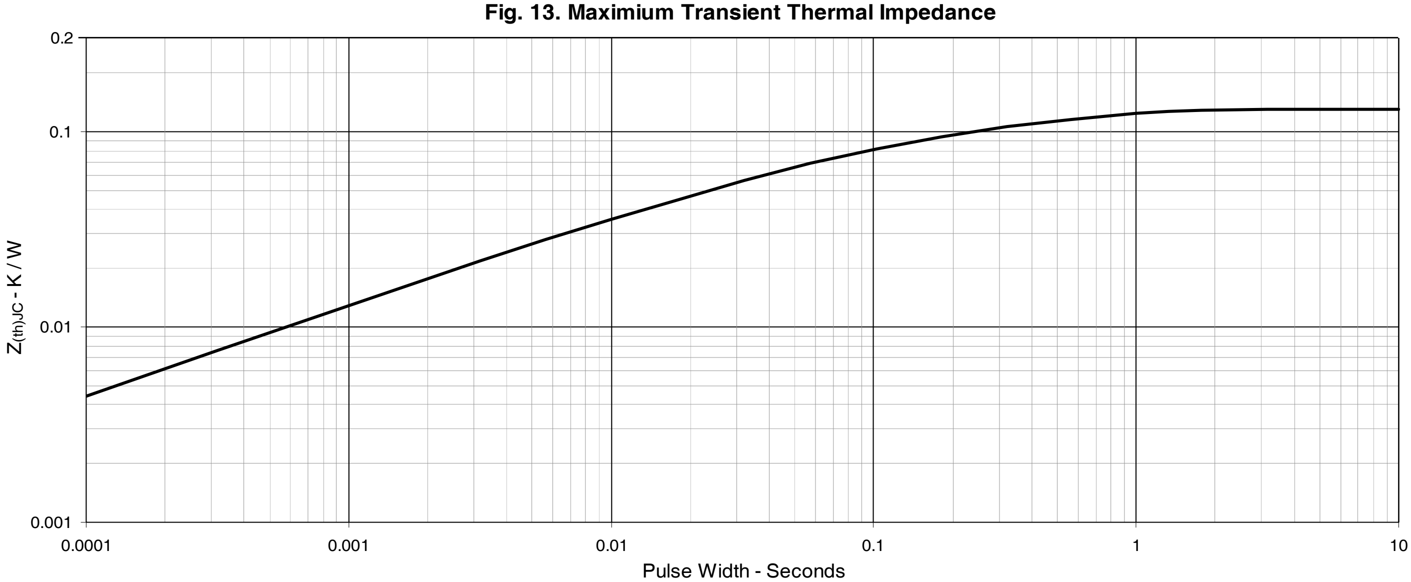
Fig. 13. Maximium Transient Thermal Impedance



IXYS REF: F_50N50P3(W7/P7) 3-29-17-A